T Number	Hits	Search Text	DB	Time stamp
L Number	1148199	((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:42
15	1140133	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		active region	IBM TDB	
16	ol	((((soi or (silicon adj on adj	USPĀT;	2002/06/11 15:38
10	_	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		active adj region	IBM_TDB	
17	0	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:39
		insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
	1	reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		transistor with active adj region	IBM_TDB	0000/06/11 15:40
18	0	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:40
		insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous and	DERWENT;	
		tft	IBM_TDB USPAT;	2002/06/11 15:40
19	20	nonporous and tft		2002/06/11 15:40
1			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
1		//// /ili adi on adi	USPAT;	2002/06/11 15:43
20	9	(((((soi or (silicon adj on adj	US-PGPUB;	2002/00/11 13.43
		insulator)) and (single-crystal adj silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous	DERWENT;	
		reducts adj atmosphere, and nonporous	IBM TDB	
21	1	{(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:44
21	1	insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous) and	DERWENT;	
		(tft or (thin adj film adj transistor))	IBM TDB	
22	1	(010 01 (01111 011) =============================	USPAT;	2002/06/11 15:48
22	_		US-PGPUB	
23	1		USPAT;	2002/06/11 16:01
			US-PGPUB	
_	673	((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:05
		(438/378)).CCLS.	US-PGPUB	
_	339	(((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:05
		(438/378)).CCLS.) and anneal\$3	US-PGPUB	
-	106	((((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 17:06
		(438/378)).CCLS.) and anneal\$3) and (soi	US-PGPUB	
		or (silicon adj on adj insulator))		0000/06/10 00 10
-	12	(((((438/311) or (438/149) or (438/150) or	USPAT;	2002/06/10 20:12
		(438/378)).CCLS.) and anneal\$3) and (soi	US-PGPUB	
		or (silicon adj on adj insulator))) and		
		(single-crystal adj silicon)	HCDAT.	2002/06/10 20:13
-	469	(soi or (silicon adj on adj insulator))	USPAT;	2002/00/10 20:13
		and (single-crystal adj silicon)	US-PGPUB USPAT;	2002/06/10 20:13
-	595	(soi or (silicon adj on adj insulator))	US-PGPUB;	2002/00/10 20:13
		and (single-crystal adj silicon)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	200	((soi or (silicon adj on adj insulator))	USPAT;	2002/06/10 20:13
-	289	and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3	EPO; JPO;	
		aimearys	DERWENT;	
			IBM TDB	
1_	285	(((soi or (silicon adj on adj insulator))	USPAT;	2002/06/10 20:14
-	205	and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3) and substrate	EPO; JPO;	
			DERWENT;	
			IBM TDB	
1	1			

-	28		USPAT;	2002/06/10 20:15
		and (single-crystal adj silicon)) and	US-PGPUB;	
		anneal\$3) and substrate) and reduc\$3 adj	EPO; JPO;	
		atmosphere	DERWENT;	
		•	IBM TDB	
-	9	(((((soi or (silicon adj on adj	USPAT;	2002/06/11 15:36
		insulator)) and (single-crystal adj	US-PGPUB;	
		silicon)) and anneal\$3) and substrate) and	EPO; JPO;	
		reduc\$3 adj atmosphere) and nonporous	DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM TDB	ļ. ;

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